

# Alkyl Monolayers on Silica Surfaces Prepared from Neat, Heated (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1-dimethylchlorosilane Analyzed by XPS

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Silane monolayers on silica, prepared from mono-, di-, and trichlorosilanes, are widely used in industry for surface functionalization and modification. However, unlike di- and trichlorosilanes, monochlorosilanes are particularly easy to work with because they can dimerize, but not polymerize, upon reaction with water. Typically, an organic solvent is used when depositing a silane monolayer. Here we show XPS spectra of monolayers of (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1-dimethylchlorosilane on silicon oxide (silicon wafer) prepared using a rapid, solvent-free approach. Reaction conditions are 60 °C for 10 min using the neat (pure) compound, and no inert atmosphere or special treatment of the compound is required. © 2004 American Vacuum Society. [DOI: 10.1116/11.20020802]

**Keywords:** *x-ray photoelectron spectroscopy; silane; alkylation; monochlorosilanes*

**PACS:** 82.80.Pv, 81.05.Lg

## INTRODUCTION

Silanes (Ref. 1) attach to silica surfaces by reacting with surface silanols (Si–OH). While monolayers prepared from monochlorosilanes are more subject to hydrolysis than those derived from di- and trichlorosilanes, surface functionalization with the monofunctionalized compounds is generally more straightforward because they cannot polymerize. Numerous preparations of silane monolayers on surfaces have been reported in the literature. For example, Maoz and Sagiv first showed that alkyl monolayers can be prepared on planar silicon using trichlorosilanes (Ref. 2). Recognizing the advantages of mono- over di- and trichlorosilanes, Rabolt and co-workers described a gas phase procedure for depositing perfluorinated alkyldimethylchlorosilanes on SiO<sub>2</sub> (Ref. 3). Both Linton and co-workers (Ref. 4) and Watts and co-workers (Ref. 5) deposited monolayers of alkyldimethylchlorosilanes, including ClSi(CH<sub>3</sub>)<sub>2</sub>(CH<sub>2</sub>)<sub>17</sub>CH<sub>3</sub> 2-tetrahydrooctyl)-1-dimethylchlorosilane, onto silica particles using an organic solvent. Typical surface modifications for know procedures call for exposing a surface to a heated, dilute solution of a silane under inert atmosphere. In contrast, here we take clean, dry, native-oxide-terminated silicon (1.5–2.0 nm), place liquid, neat (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1-dimethylchlorosilane on its surface, and heat it in an oven at 60 °C for 10 min (relative humidity= 70%). After reacting, the surface is cleaned, dried, loaded into an XPS UHV chamber, and analyzed by XPS, which showed carbon levels consistent with monolayer quantities of surface alkyl chains (ellipsometric thickness is approximately 0.6–0.7 nm, advancing contact angle  $\theta_a=103.2^\circ \pm 0.5^\circ$ , receding contact angle ( $\theta_r$ )=86.8°±2.5°). The results of using this new facit surface silanization technique (for 5 different silanes) is summarized in a note published in Langmuir (Ref. 6).

## SPECIMEN DESCRIPTION

**Host Material:** Monolayer (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1 dimethylchlorosilane/Si

**CAS Registry #:** 102448-47-1

**Accession #** 00767

**Technique:** XPS

**Host Material:** Monolayer (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1 dimethylchlorosilane/Si

**Instrument:** Surface Science Laboratories, Inc. SSX-100

**Major Elements in Spectrum:** C, Si, O, F

**Minor Elements in Spectrum:** none

**Printed Spectra:** 5

**Spectra in Electronic Record:** 5

**Spectral Category:** technical

**Host Material Characteristics:** homogeneous; solid; single crystal; semiconductor; ceramic; glass; thin film; coating

**Chemical Name:** silicon/silicon oxide

**Source:** Montco Silicon Technologies, Inc.

**Host Composition:** Si/SiO<sub>2</sub>

**Form:** single crystal wafer, *p*-type

**Lot #:** W9969

**Structure:** Si (100)

**As Received Condition:** not specified

**Analyzed Region:** same as host material

**Ex Situ Preparation/Mounting:** The silicon surfaces were first cleaned with a solution of NH<sub>4</sub>OH (conc.): H<sub>2</sub>O<sub>2</sub> (conc.) (50:50) (v/v) for 30 min at room temperature. They were then rinsed with water and finally washed with 5% vol. HCl (conc.) for 1 h. After reaction in the oven (for 10 min at 60 °C), the wafers were rinsed with acetone, cleaned with a soft artists brush using a 2% sodium dodecyl sulfate solution in water, and placed in a Soxhlet apparatus overnight using *m*-xylene (b.p. ~139 °C) as the extraction solvent. The samples were then removed from the Soxhlet, rinsed with water, dried, and mounted into the XPS machine. (Note: source beam size on the instrument was not well characterized and may be up to twice as large as the manufacturer's values given here [See Source Beam Size at Specimen Surface].) Warning: this procedure should not be attempted with volatile silanes. Fumes from a volatile organic compound are potentially explosive. In addition, the NH<sub>4</sub>OH/H<sub>2</sub>O<sub>2</sub> cleaning solution is extremely caustic and should be used with great care.

**In Situ Preparation:** none

**Charge Control:** none

**Temp. During Analysis:** 298 K

**Pressure During Analysis:** <2.053×10<sup>-7</sup> Pa

## INSTRUMENT DESCRIPTION

**Manufacturer and Model:** Surface Science Laboratories, Inc.  
SSX-100

**Analyzer Type:** spherical sector

**Detector:** resistive anode position detector

**Number of Detector Elements:** 128

## INSTRUMENT PARAMETERS COMMON TO ALL SPECTRA

### ■ Spectrometer

**Analyzer Mode:** constant pass energy

**Throughput ( $T=E^M$ ):**  $N=0$

**Excitation Source Window:** 10  $\mu\text{m}$  Mylar

**Excitation Source:** Al  $K_\alpha$  monochromatic

**Source Energy:** 1486.6 eV

**Source Strength:** 200 W

**Source Beam Size:** 0.8 mm  $\times$  0.8 mm

**Signal Mode:** multichannel direct

### ■ Geometry

**Incident Angle:** 55°

**Source to Analyzer Angle:** 70.8°

**Emission Angle:** 55°

**Specimen Azimuthal Angle:** 0°

**Acceptance Angle from Analyzer Axis:** 30°

**Analyzer Angular Acceptance Width:** 30°  $\times$  30°

## ACKNOWLEDGMENTS

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## REFERENCES

1. E. P. Plueddemann, *Silane Coupling Agents* (Plenum, New York, 1991).
2. R. Maoz and J. Sagiv, *J. Colloid Interface Sci.* **100**, 465 (1984).
3. P. W. Hoffmann, M. Stelzle, and J. F. Rabolt, *Langmuir* **13**, 1877 (1997).
4. S. J. Simko, M. L. Miller, and R. W. Linton, *Anal. Chem.* **57**, 2448 (1985).
5. V. A. Brown, D. A. Barrett, P. N. Shaw, M. C. Davies, H. J. Ritchie, P. Ross, A. J. Paul, and J. F. Watts, *Surf. Interface Anal.* **21**, 263 (1994).
6. G. A. Hussein, J. Peacock, A. Sathyapalan, L. W. Zilch, M. C. Asplund, E. T. Sevy, and M. R. Linford, *Langmuir* **19**, 5169 (2003).

SPECTRAL FEATURES TABLE

Spectrum ID #	Element/Transition	Peak Energy (eV)	Peak Width FWHM (eV)	Peak Area (counts)	Sensitivity Factor	Concentration (at. %)	Peak Assignment
00767-02	Si 2p	99.4	1.3	13783	0.9	29.9	...
00767-03	C 1s	291.9	2.2	12714	1.00	17.4	...
00767-04	O 1s	532.2	2.3	30383	2.49	28.1	...
00767-05	F 1s	688.9	3.2	49287	3.32	28.9	...

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**ANALYZER CALIBRATION TABLE**

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<b>Spectrum ID #</b>	<b>Element/ Transition</b>	<b>Peak Energy (eV)</b>	<b>Peak Width FWHM (eV)</b>	<b>Peak Area (counts)</b>	<b>Sensitivity Factor</b>	<b>Concentration (at. %)</b>	<b>Peak Assignment</b>
... <sup>a</sup>	Au 4 <i>f</i> <sub>7/2</sub>	83.92	0.98	2200	10.67	...	...
... <sup>b</sup>	Au 4 <i>f</i> <sub>7/2</sub>	83.92	1.6	6000	10.67	...	...
... <sup>c</sup>	Cu 3 <i>s</i>	122.36	3.0	1600	1.05	...	...
... <sup>b</sup>	Cu 2 <i>p</i> <sub>3/2</sub>	932.45	1.78	4000	9.73	...	...

<sup>a</sup> Spot size 300 μm, pass energy 50 eV, 2 scans

<sup>b</sup> Spot size 800 μm, pass energy 150 eV, 1 scan

<sup>c</sup> Spot size 800 μm, pass energy 150 eV, 3 scans

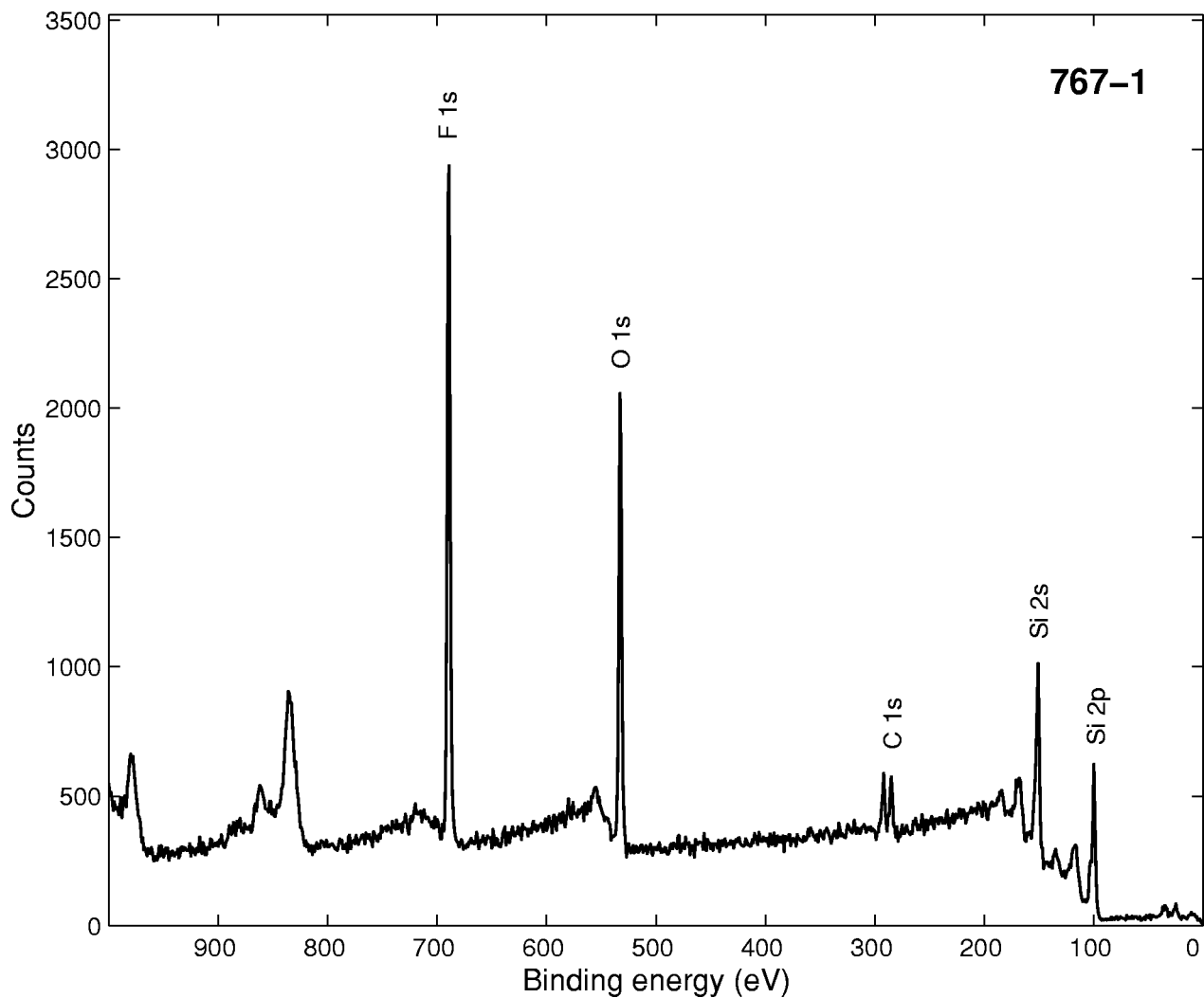
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**GUIDE TO FIGURES**

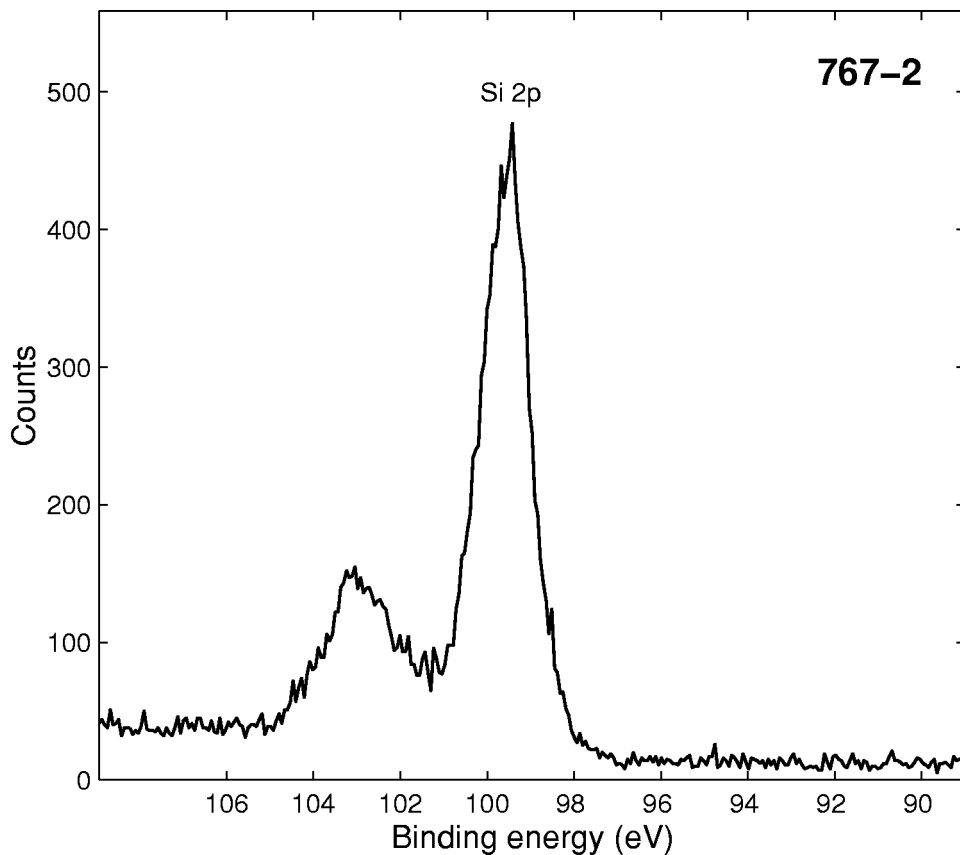
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<b>Spectrum (Accession) #</b>	<b>Spectral Region</b>	<b>Voltage Shift*</b>	<b>Multiplier</b>	<b>Baseline</b>	<b>Comment #</b>
<b>767-1</b>	Survey	0	1	0	
<b>767-2</b>	Si 2 <i>p</i>	0	1	0	
<b>767-3</b>	C 1 <i>s</i>	0	1	0	
<b>767-4</b>	O 1 <i>s</i>	0	1	0	
<b>767-5</b>	F 1 <i>s</i>	0	1	0	

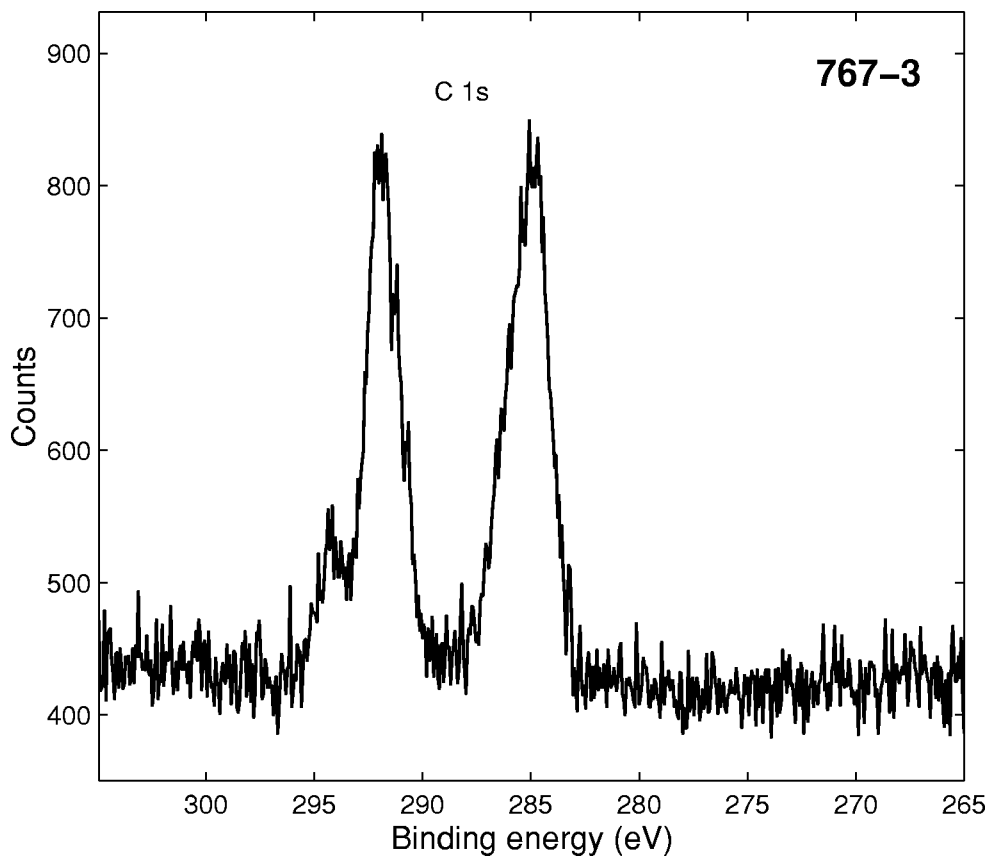
\* Voltage shift of the archived (as-measured) spectrum relative to the printed figure. The figure reflects the recommended energy scale correction due to a calibration correction, sample charging, flood gun, or other phenomenon.



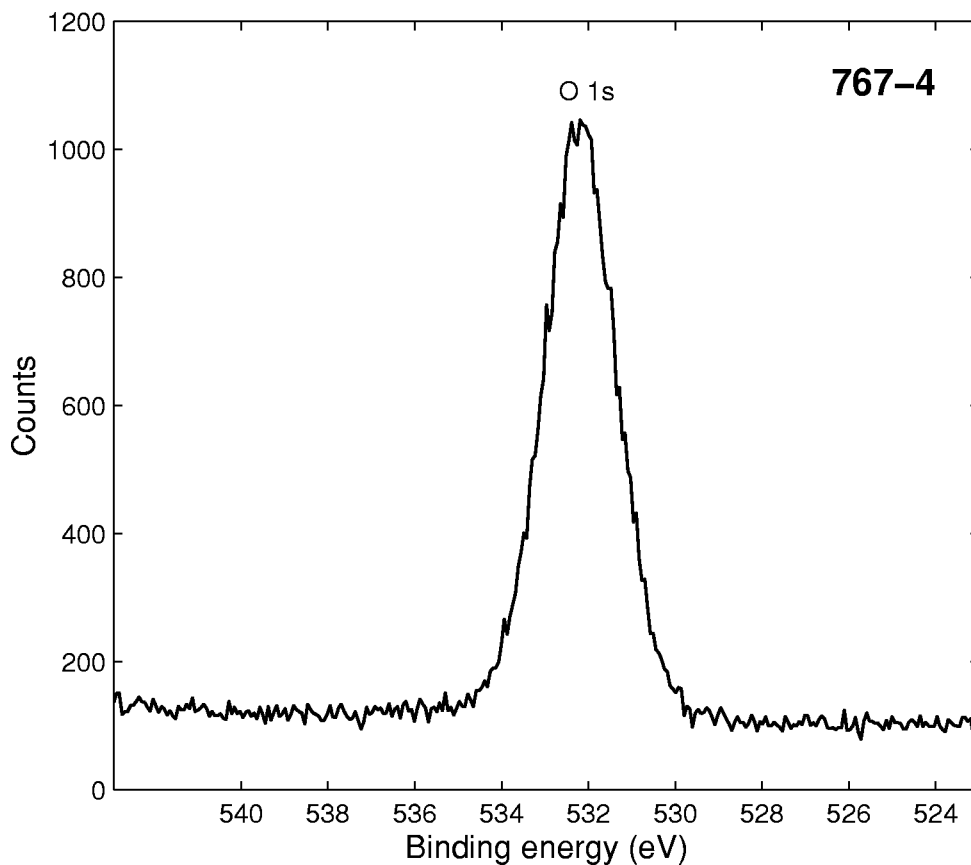
<b>Accession #</b>	<b>00767-01</b>
<b>Host Material</b>	Monolayer (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1 dimethylchlorosilane/Si
<b>Technique</b>	XPS
<b>Spectral Region</b>	survey
<b>Instrument</b>	Surface Science Laboratories, Inc. SSX-100
<b>Excitation Source</b>	Al $K_{\alpha}$ monochromatic
<b>Source Energy</b>	1486.6 eV
<b>Source Strength</b>	200 W
<b>Source Size</b>	0.8 mm $\times$ 0.8 mm
<b>Analyzer Type</b>	spherical sector
<b>Incident Angle</b>	55°
<b>Emission Angle</b>	55°
<b>Analyzer Pass Energy</b>	150 eV
<b>Analyzer Resolution</b>	1.5 eV
<b>Total Signal Accumulation Time</b>	1320 s
<b>Total Elapsed Time</b>	1520 s
<b>Number of Scans</b>	6
<b>Effective Detector Width</b>	15.1 eV
<b>Analyzer Width</b>	1500 $\mu\text{m}$ $\times$ 12000 $\mu\text{m}$
<b>Comment</b>	note C 1s split peak and a strong F 1s peak



**Accession #:** 00767-02  
**Host Material:** Monolayer  
 (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1  
 dimethylchlorosilane/Si  
**Technique:** XPS  
**Spectral Region:** Si 2p  
 Instrument: Surface Science  
 Laboratories, Inc. SSX-100  
 Excitation Source: Al  $K_{\alpha}$   
 monochromatic  
 Source Energy: 1486.6 eV  
 Source Strength: 200 W  
 Source Size: 0.8 mm  $\times$  0.8 mm  
 Incident Angle: 55°  
 Analyzer Type: spherical sector  
 Analyzer Pass Energy: 50 eV  
 Analyzer Resolution: 0.5 eV  
 Emission Angle: 55°  
 Total Signal Accumulation Time:  
 368 s  
 Total Elapsed Time: 537 s  
 Number of Scans: 6  
 Effective Detector Width: 6.09 eV  
 Analyzer Width: 750  $\mu\text{m}$   $\times$   
 6000  $\mu\text{m}$



**Accession #:** 00767-03  
**Host Material:** Monolayer  
 (Tridecafluoro-1,1,2,2-tetrahydrooctyl)-1  
 dimethylchlorosilane/Si  
**Technique:** XPS  
**Spectral Region:** C 1s  
 Instrument: Surface Science  
 Laboratories, Inc. SSX-100  
 Excitation Source: Al  $K_{\alpha}$   
 monochromatic  
 Source Energy: 1486.6 eV  
 Source Strength: 200 W  
 Source Size: 0.8 mm  $\times$  0.8 mm  
 Incident Angle: 55°  
 Analyzer Type: spherical sector  
 Analyzer Pass Energy: 50 eV  
 Analyzer Resolution: 0.5 eV  
 Emission Angle: 55°  
 Total Signal Accumulation Time:  
 1227 s  
 Total Elapsed Time: 1396 s  
 Number of Scans: 20  
 Effective Detector Width: 6.09 eV  
 Analyzer Width: 750  $\mu\text{m}$   $\times$  6000  
 $\mu\text{m}$   
 Comment: Three carbon species  
 are visible:  $-\text{CH}_2$ ,  $-\text{CF}_2$ ,  $-\text{CF}_3$



■ **Accession #:** 00767-04  
 ■ **Host Material:** Monolayer  
 (Tridecafluoro-1,1,2,2-  
 tetrahydrooctyl)-1  
 dimethylchlorosilane/Si  
 ■ **Technique:** XPS  
 ■ **Spectral Region:** O 1s

Instrument: Surface Science  
 Laboratories, Inc. SSX-100

Excitation Source: Al  $K_{\alpha}$   
 monochromatic

Source Energy: 1486.6 eV

Source Strength: 200 W

Source Size: 0.8 mm  $\times$  0.8 mm

Incident Angle: 55°

Analyzer Type: spherical sector

Analyzer Pass Energy: 50 eV

Analyzer Resolution: 0.5 eV

Emission Angle: 55°

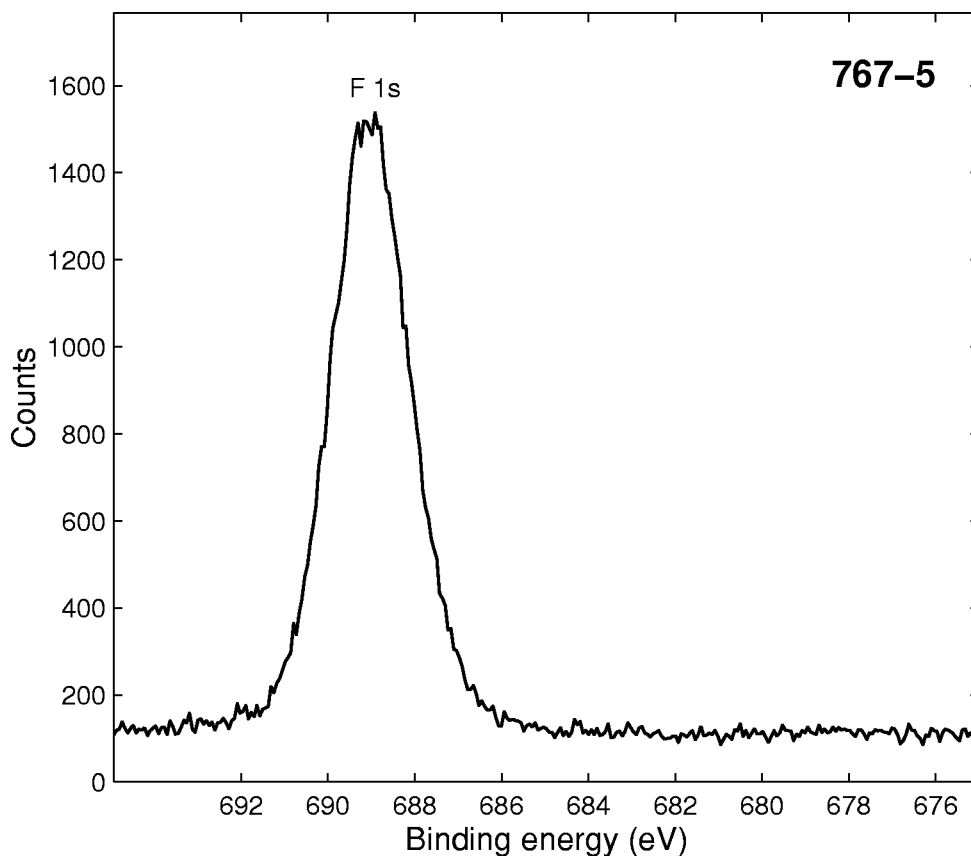
Total Signal Accumulation Time:  
 368 s

Total Elapsed Time: 537 s

Number of Scans: 6

Effective Detector Width: 6.09 eV

Analyzer Width: 750  $\mu\text{m}$   $\times$  6000  
 $\mu\text{m}$



■ **Accession #:** 00767-05  
 ■ **Host Material:** Monolayer  
 (Tridecafluoro-1,1,2,2-  
 tetrahydrooctyl)-1  
 dimethylchlorosilane/Si

■ **Technique:** XPS

■ **Spectral Region:** F 1s

Instrument: Surface Science  
 Laboratories, Inc. SSX-100

Excitation Source: Al  $K_{\alpha}$   
 monochromatic

Source Energy: 1486.6 eV

Source Strength: 200 W

Source Size: 0.8 mm  $\times$  0.8 mm

Incident Angle: 55°

Analyzer Type: spherical sector

Analyzer Pass Energy: 50 eV

Analyzer Resolution: 0.5 eV

Emission Angle: 55°

Total Signal Accumulation Time:  
 368 s

Total Elapsed Time: 537 s

Number of Scans: 6

Effective Detector Width: 6.09 eV

Analyzer Width: 750  $\mu\text{m}$   $\times$  6000  
 $\mu\text{m}$